

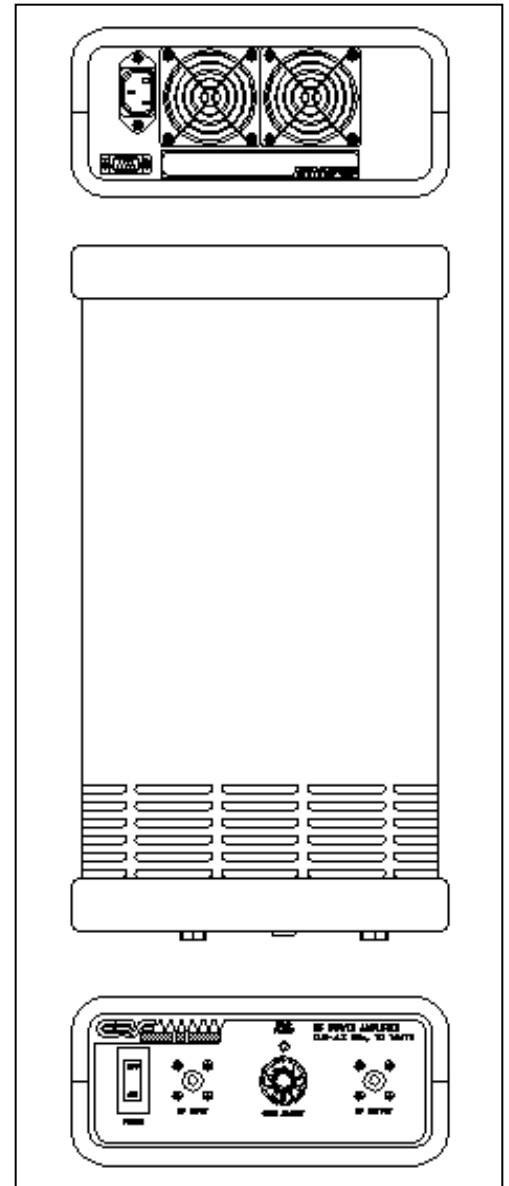
Designed for ultra broadband high power linear applications, this amplifier utilizes linear GaAsFET Power devices that provide high gain, wide dynamic range and excellent linearity. Exceptional performance, long term reliability and high efficiency are achieved by employing advanced broadband RF matching networks and combining techniques, built in high quality power supply, EMI/RFI filters, Aluminum machined housings and qualified components. Each unit undergoes extensive burn-in prior to final test and Q/A.

ELECTRICAL SPECIFICATIONS

Characteristics	Rating	Limit
Frequency Response	1000 – 2000 MHz	Min
Power Output CW	12 Watts	Min
Power Output @ 1 dB comp.	10 Watts	Min
Small Signal Gain	42 dB	Min
Small Signal Gain Flatness	±1.5 dB	Max
Third Order Intercept Point	+48 dBm	Typ
Input Overdrive	+10 dBm	Max
Input/Output VSWR @ 50 ohm	2:1	Max
Harmonics @ 1 dB compression	-20 dBc	Typ
Noise Figure	10 dB	Max
Spurious Signals	-60 dBc	Max
Supply Voltage (single phase)	100 - 240 VAC	Nom
Power Consumption	150 Watts AC	Max

MECHANICAL SPECIFICATIONS

Dimensions (Bench Top)	8.5"x3.5"x16"	Max
Weight	20 lb.	Max
RF Connectors	Type-N front panel	
Cooling	Internal forced-air	



HD Communications

Solid State Broadband High Power RF Amplifier HD17490 1000 – 2000 MHz / 12 Watts

ENVIRONMENTAL CHARACTERISTICS

Operating Temperature: 0°C to +50°C

Non-operating Temperature: -40°C to +85°C

Humidity: 95% relative without condensation

Altitude: 10,000 feet

Shock and Vibration: Normal truck transport

CIRCUIT PROTECTIONS

Infinite Load VSWR

RF Input Overdrive

Thermal Overload

AVAILABLE OPTIONS

- Front or Rear Panel Connectors
- Rack Mount or different Case Style
- Rack Mounting Slide
- Extended Temperature Range
- LCD Digital Display
 - Forward and Reverse indication
 - Fault indication
 - Modules status indication
 - Gain Adjustment
 - Automatic Level Control
 - Standby Mode
- IEEE-488.2 GPIB interface